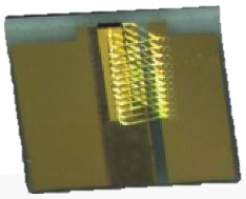
High Power RSOA Chip on Carriers

Part Number: COC-286



High Power RSOA Chip on Carrier
Single-Mode RSOA Curved Waveguide
Wavelength at 1550nm

Features

- High Output Power
- High Dynamic Range
- High Efficiency
- Standard RSOA Chip on Carrier
- Cost Effective

Application

- Optical Communications
- LiDAR
- Free Space Communications
- Network Test Equipment

SemiNex delivers the highest available power at infrared wavelengths between 12xx and 19xx nm. When necessary, we will further optimize the design of our InP & GaSb laser chips to meet our customers' specific optical and electrical performance needs. Diodes, bars and packages are tested to meet customer and market performance demands. Typical results and packaging options are shown. Contact SemiNex for additional details or to discuss your specific requirements.

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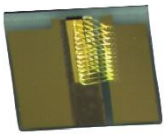
Specification

COC-286



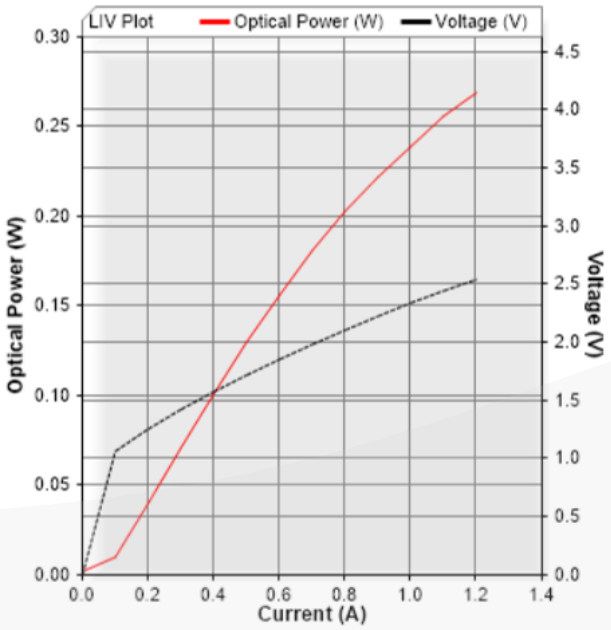
Optical	Symbol	Typ.	Units
Center Wavelength	λ_c	1550	nm
ASE Output Power @ 1A	Pout	0.2	watts
Aperture Width	AW	4	µm
Spectral Width	$\Delta\lambda$	85	nm @ 3dB
Beam Exit Angle	θ_{EXT}	19.5	Degree
Fast Axis Div.	$\Theta_{\perp}$	30	Deg FWHM
Slow Axis Div.	$\Theta_{\parallel}$	20	Deg FWHM
Front Facet Reflectivity		<0.1%	
Rear Face Reflectivity		98%	
Waveguide		Curved	
Electrical	**Symbol**		**Units**
Operating Current	I_{op}	1	A
Operating Voltage	V_{op}	2	V
Mechanical		**Range**	**Units**
Chip Width		500	µm
Operating Temp.**		-20 to 75	°C
Storage Temp.		-40 to 85	°C

*Specified values are rated at a constant heat sink temperature of 20°C.
**High temperature operation will reduce performance and MTTF.
Unless otherwise indicated all values are nominal.

SemiNex RSOA COC-286

Graphs & Data

Typical ASE L-I-V Characteristics



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Mechanical Drawing